

FIG.1

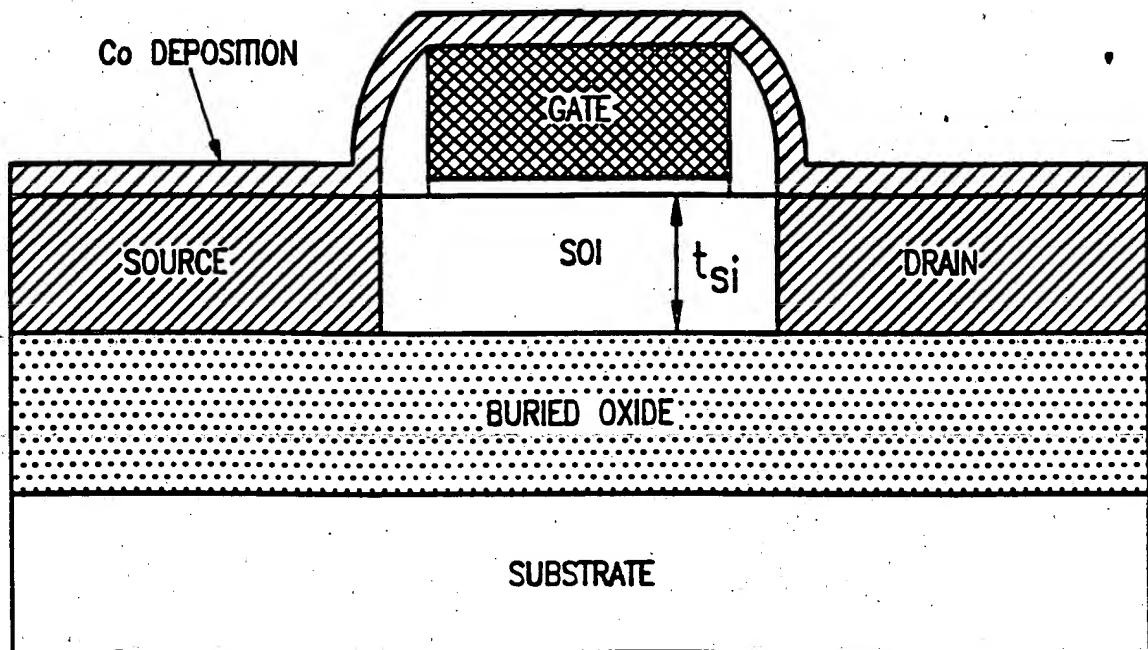


FIG.2

use 2<sup>nd</sup> set

099044-0110

FORM  $\text{Co}_2\text{Si}$  BY LOW TEMPERATURE ANNEAL

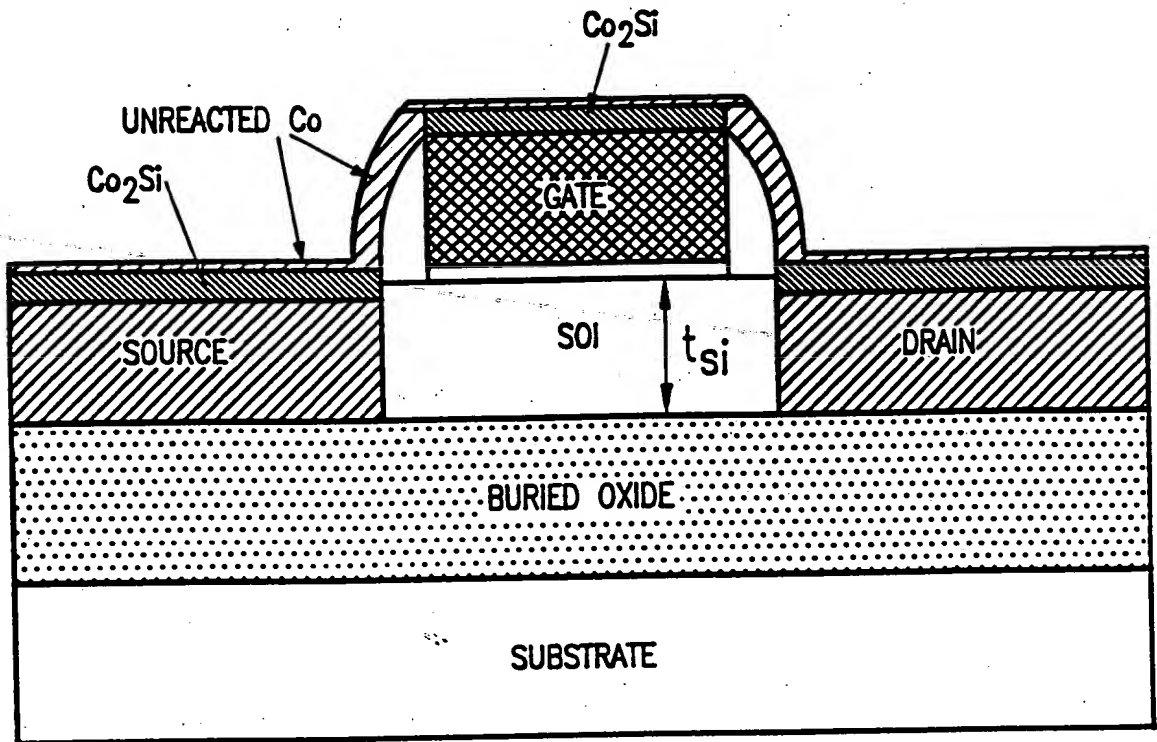


FIG.3

DEPOSITE  $\alpha\text{-Si}$

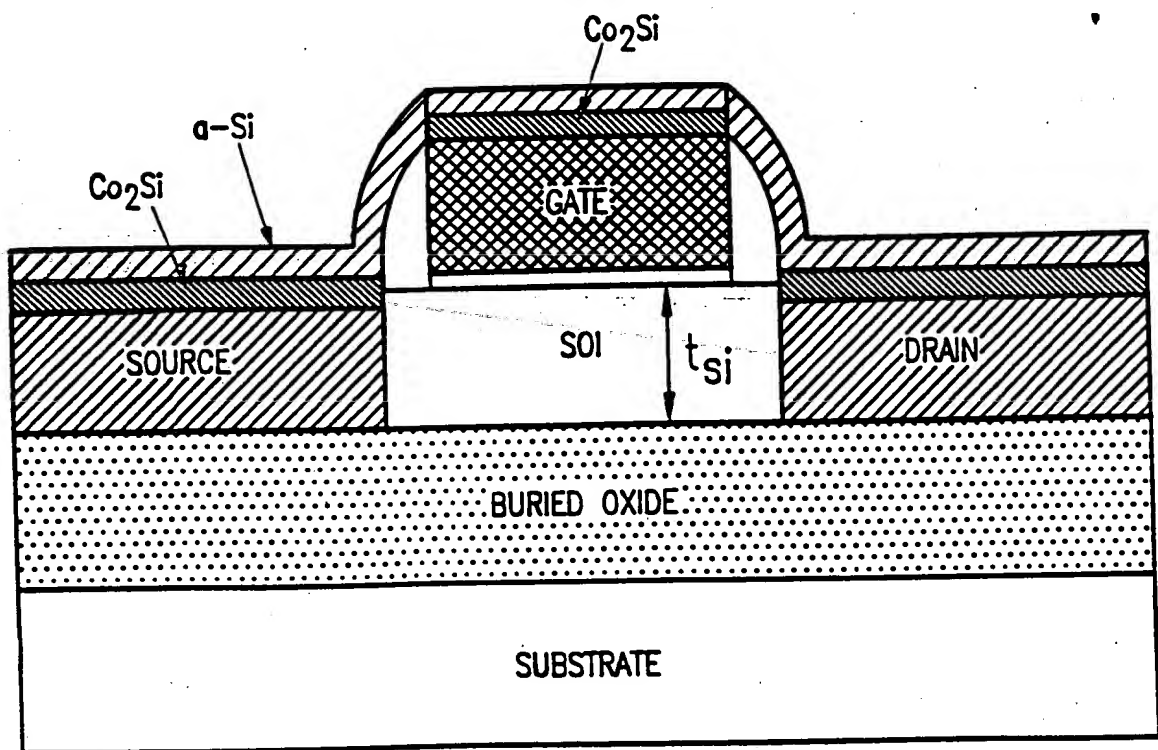


FIG.4

09902483.07.1101  
TOT 40" E8420650

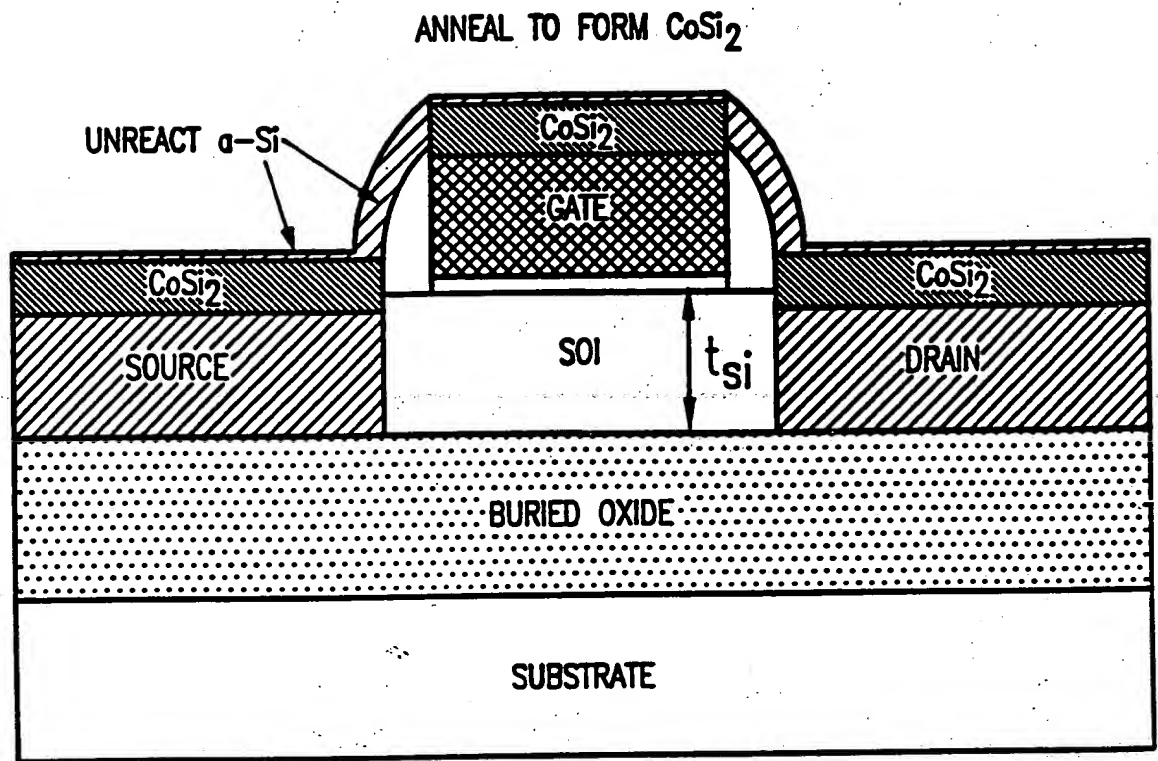


FIG.5

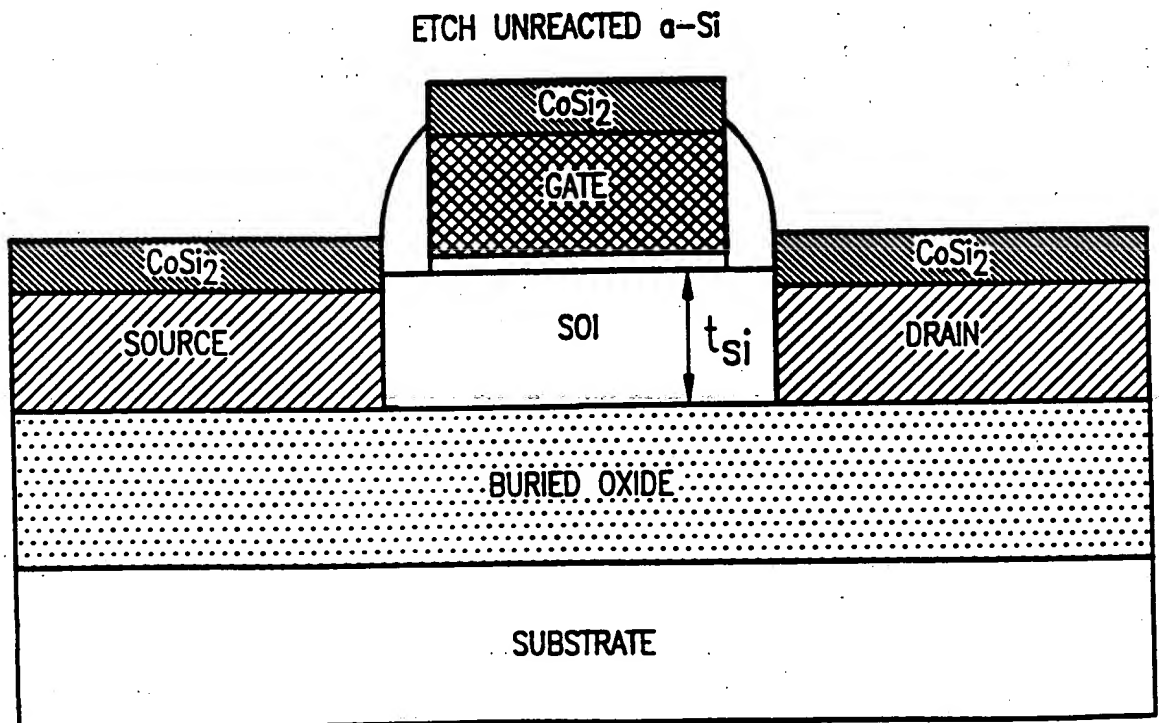


FIG.6

09002483-071101  
TOT 40-EB420660

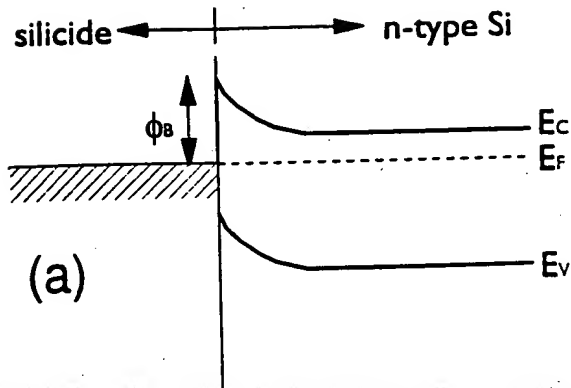


Fig. 7 (a)

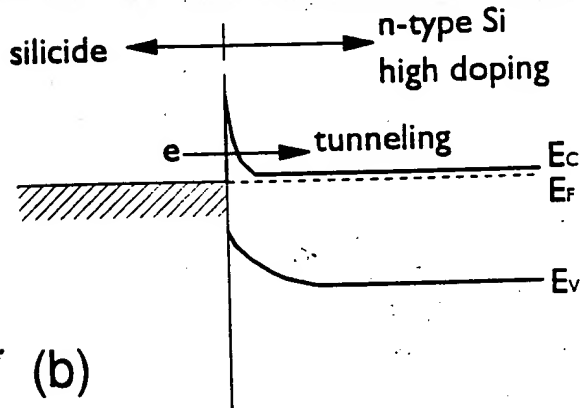
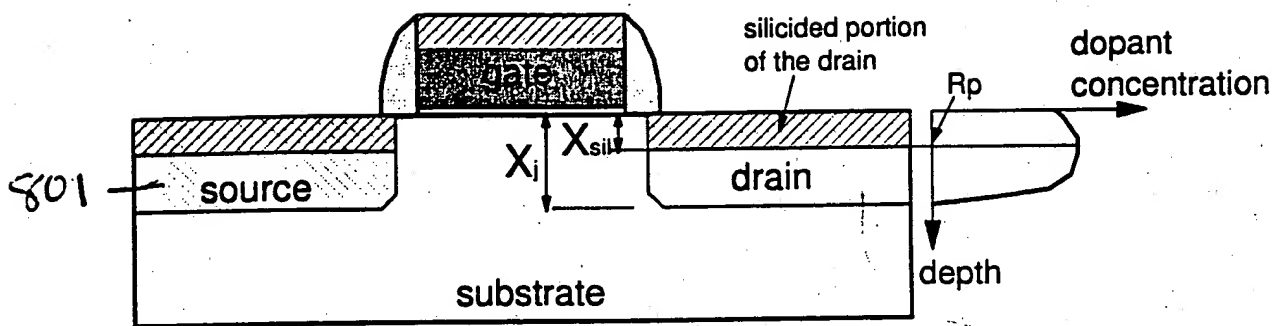


Fig. 7 (b)

0902483-071101



$X_j$  = source or drain junction depth

$X_{sil}$  = silicide junction depth

$R_p$  = peak dopant concentration

Requirements:

1.  $X_j > X_{sil}$
2.  $X_{sil}$  roughly equals  $R_p$

Figure 8

09902483-071101

